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Active L1: (3796) (opening trench via hole recess) with ((plasma gas) near (h2 hydrogen)) L2: (78) 1 and (opening trench via hole recess) with ((plasma gas) near (chlorine)) L6: (2) 5 and (opening trench via hole recess) with (silicide) L5: (18) 2 and (opening trench via hole recess) with (insulat\$3 dielectric) Failed	Second Second Close Cl

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1	p	r US	2005021		Method of fabricating	;438/270			Numazawa, Sumito	_	_	_		_ : ,	
		2005003.757			semiconductor device.			i	เคาลเ		i •				
2	p :		2004082		METHOD OF	:438/589	257/E21.4		Numazawa, Sumito	г	_	_	-	٦,	- -
1		2004016665			FABRICATING SEMIC.		1.9:		et al.				1	- 7	
3	p :	US	2003070		Method of fabricating	438/270	257/E21.4		Numazawa, Sumito	г	_	_	-	ر! ر	-
		2003012480			semiconductor device		19:		et al.		:		1	:	1
4	p :	r US	:2003011	23	Process for fabricating	438/706	257/E21.2		Negishi, Nobuyuki	_	_	_		٠: ١	- -
		2003001331.	.6		semiconductor device		52:		int of				: :	•	
5	p :	r:US	2002072		Method of fabricating	438/270	257/E21.4		Numazawa, Sumito	г	_	г.	-	٠ : ١	- -
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6	P :	r :US	2002012		Method of fabricating	438/589	257/288;		Numazawa, Sumito	г	r :	_	- 1	٠. ١	-
	<u>i</u>	2002000986			semiconductor device		25.7/33.0:		et.al.		:			!	
7	P	L US 6803281	2004101		Method of fabricating	:438/270	257/288;		Numazawa; Sumito	_	۲ :	_	_	٠: ١	- -
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8	P .	LUS 6720220	2004041		<u>. </u>	438/270	257/288;		Numazawa; Sumito	г	<u>ا</u> ا	г	-	- i	- İ -
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9	P .	L US 6645870	.2003111		_	438/710	257/E21.2		Negishi; Nobuyuki	г	: ٦	_	إحا	٠; ١	-
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111	₽ :	US 6410959	2002062		•	257/330	257/341;		Numazawa; Sumito	г	_	r.	_	- :	- - '
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12	-	US 6307231	2001102	Method of fabricating	257/330	257/341;	1	Numazawa; Sumito	_	_	_	-	- ! -	
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13	₅	_ US 6168996	2001010	Method of fabricating	438/270	257/330;		Numazawa; Sumito	-	-	_	-	ے! ہے	. _
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14	-	_ US 5458858	1995101	Integrated procedure for	422/234	422/129;		Dawkins; John L.	_	-	-		רוְר	. _
	ļ.,	A	7	high vield production of		422/200:			<u>.</u>					1.
15	=	_ US 5324497	1994062	Integrated procedure for	423/478	204/277;		Westerlund; G.	-	-	_	-	r į r	
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16	5	US 4935800	1990061	Semiconductor integrated	257/520	257/378;		Taguchi; Minoru	_	-	· -	!	r r	
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17	-	_ JP	2001051	METHOD OF	1	1		ODA, KATSUYA	-	-	-	-	г	. _
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